Geometric Programming and Its Applications to EDA Problems

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Outline

- Basic approach
- Geometric programming & generalized geometric programming
- Digital circuit design applications
- Analog and RF circuit design applications
- Monomial and posynomial fitting
- Conclusions

Basic Approach

Basic approach

- 1. formulate circuit design problem as **geometric program** (GP), an optimization problem with special form
- 2. solve GP using specialized, tailored method

- this tutorial focuses on step 1 (a.k.a. **GP modeling**)
- step 2 is **technology**

Why?

- we can solve even large GPs very effectively, using recently developed methods
- so once we have a GP formulation, we can solve circuit design problem effectively

we will see that

- GP is especially good at handling a large number of concurrent constraints
- GP formulation is useful even when it is approximate

Trade-offs in optimization

- general trade-off between generality and effectiveness
- generality
 - number of problems that can be handled
 - accuracy of formulation
 - ease of formulation
- effectiveness
 - speed of solution, scale of problems that can be handled
 - global vs. local solutions
 - reliability, baby-sitting, starting point

Example: least-squares vs. simulated annealing

least-squares

- large problems reliably (globally) solved quickly
- no initial point, no algorithm parameter tuning
- solves very restricted problem form
- with tricks and extensions, basis of vast number of methods that work (control, filtering, regression, . . .)

simulated annealing

- can be applied to any problem (more or less)
- slow, needs tuning, babysitting; not global in practice
- method of choice for some problems you can't handle any other way

Where GP fits in

somewhere in between, closer to least-squares . . .

- like least-squares, large problems can be solved reliably (globally), no starting point, tuning, . . .
- solves a class of problems broader than least-squares, less general than simulated annealing
- formulation takes effort, but is fun and has high payoff

Geometric Programming & Generalized Geometric Programming

Monomial & posynomial functions

 $x = (x_1, \dots, x_n)$: vector of positive optimization variables

• function g of form

$$g(x) = cx_1^{\alpha_1} x_2^{\alpha_2} \cdots x_n^{\alpha_n},$$

with c > 0, $\alpha_i \in \mathbf{R}$, is called **monomial**

ullet sum of monomials, i.e., function f of form

$$f(x) = \sum_{k=1}^{t} c_k x_1^{\alpha_{1k}} x_2^{\alpha_{2k}} \cdots x_n^{\alpha_{nk}},$$

with $c_k > 0$, $\alpha_{ik} \in \mathbb{R}$, is called **posynomial**

Examples

with x, y, z variables,

- 0.23, $2z\sqrt{x/y}$, $3x^2y^{-.12}z$ are monomials (hence also posynomials)
- 0.23 + x/y, $2(1+xy)^3$, 2x + 3y + 2z are posynomials
- 2x + 3y 2z, $x^2 + \tan x$ are neither

Generalized posynomials

f is a **generalized posynomial** if it can be formed using addition, multiplication, positive power, and maximum, starting from posynomials

examples:

- $\max\{1+x_1,2x_1+x_2^{0.2}x_3^{-3.9}\}$
- $(0.1x_1x_3^{-0.5} + x_2^{1.7}x_3^{0.7})^{1.5}$
- $\left(\max\left\{1+x_1,2x_1+x_2^{0.2}x_3^{-3.9}\right\}\right)^{1.7}+x_2^{1.1}x_3^{3.7}$

Composition rules

- monomials closed under product, division, positive scaling, power, inverse
- **posynomials** closed under sum, product, positive scaling, division by monomial, positive integer power
- **generalized posynomials** closed under sum, product, max, positive scaling, division by monomial, positive power

Generalized geometric program (GGP)

minimize
$$f_0(x)$$

subject to $f_i(x) \leq 1, \quad i = 1, \dots, m$
 $g_i(x) = 1, \quad i = 1, \dots, p$

 f_i are **generalized posynomials**, g_i are monomials

- \bullet called **geometric program (GP)** when f_i are **posynomials**
- a highly nonlinear constrained optimization problem

GP example

- ullet maximize volume of box with width w, height h, depth d
- ullet subject to limits on wall and floor areas, aspect ratios h/w, d/w

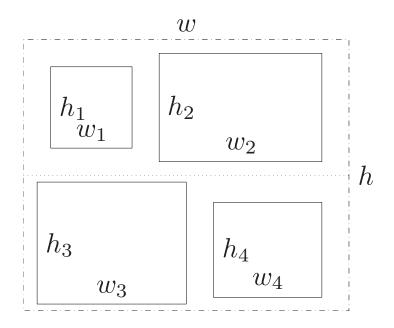
maximize
$$hwd$$
 subject to $2(hw+hd) \leq A_{\mathrm{wall}}, \quad wd \leq A_{\mathrm{flr}}$ $\alpha \leq h/w \leq \beta, \quad \gamma \leq d/w \leq \delta$

in standard GP form:

minimize
$$h^{-1}w^{-1}d^{-1}$$
 subject to $(2/A_{\mathrm{wall}})hw + (2/A_{\mathrm{wall}})hd \leq 1, \quad (1/A_{\mathrm{flr}})wd \leq 1$ $\alpha h^{-1}w \leq 1, \quad (1/\beta)hw^{-1} \leq 1$ $\gamma wd^{-1} \leq 1, \quad (1/\delta)w^{-1}d \leq 1$

GGP example: Floor planning

- choose cell widths, heights
- fixed cell areas
- (1 left of 2) above (3 left of 4)
- aspect ratio constraints
- minimize bounding box area



minimize
$$hw$$

subject to $h_i w_i = A_i, \quad 1/\alpha_{\max} \le h_i/w_i \le \alpha_{\max}, \\ \max\{h_1, h_2\} + \max\{h_3, h_4\} \le h, \\ \max\{w_1 + w_2, w_3 + w_4\} \le w$

...a GGP

Trade-off analysis

(no equality constraints, for simplicity)

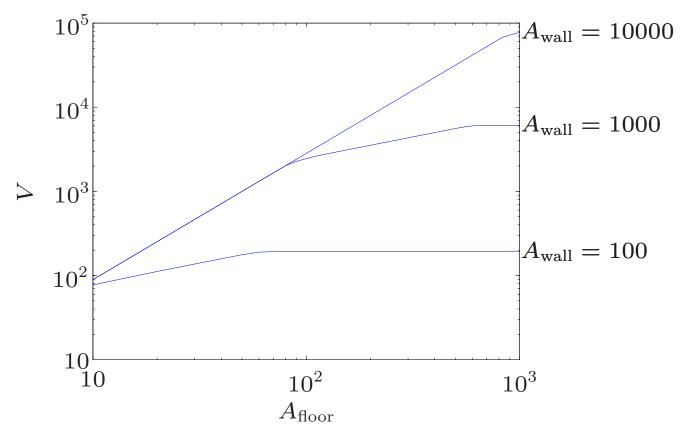
• form perturbed version of original GP, with changed righthand sides:

minimize
$$f_0(x)$$

subject to $f_i(x) \leq u_i, \quad i = 1, \dots, m$

- $u_i > 1$ ($u_i < 1$) means *i*th constraint is relaxed (tightened)
- let p(u) be optimal value of perturbed problem
- plot of p vs. u is (globally) **optimal trade-off surface** (of objective against constraints)

Trade-off curves for maximum volume box example



- ullet maximum volume V vs. A_{flr} , for $A_{\mathrm{wall}}=100,\ 1000,\ 10000$
- h/w, d/w aspect ratio limits 0.5, 2

Sensitivity analysis

optimal sensitivity of ith constraint is

$$S_i = \frac{\partial p/p}{\partial u_i/u_i}\bigg|_{u=1}$$

- S_i predicts fractional change in optimal objective value if ith constraint is (slightly) relaxed or tightened
- very useful in practice; give quantitative measure of how tight a binding constraint is
- when we solve a GP we get all optimal sensitivities at no extra cost

Example

minimize circuit delay, subject to power, area constraints (details later)

minimize
$$D(x)$$
 subject to $P(x) \leq P^{\max}$, $A(x) \leq A^{\max}$

- both constraints tight at optimal x^* : $P(x^*) = P^{\max}$, $A(x^*) = A^{\max}$
- suppose optimal sensitivities are $S^{\mathrm{pwr}} = -2.1$, $S^{\mathrm{area}} = -0.3$
- we predict:
 - for 1% increase in allowed power, optimal delay decreases 2.1%
 - for 1% increase in allowed area, optimal delay decreases 0.3%

GP and **GGP** attributes

- after log transform of variables/constraints, they become convex problems
- can convert GGP to GP, e.g., $f(x) + \max\{g(x), h(x)\} \le 1$ becomes

$$f(x) + t \le 1$$
, $g(x)/t \le 1$, $h(x)/t \le 1$

where t is new (dummy) variable

- conversion tricks can be automated
 - parser scans problem description, forms GP
 - efficient GP solver solves GP
 - solution transformed back (dummy variables eliminated)

How GPs are solved

the practical answer: none of your business

more politely: you don't need to know

it's technology:

- good algorithms are known
- good software implementations are available

How GPs are solved

- work with log of variables: $y_i = \log x_i$
- take log of monomials/posynomials to get

minimize
$$\log f_0(e^y)$$

subject to $\log f_i(e^y) \leq 0, \quad i = 1, \dots, m$
 $\log g_i(e^y) = 0, \quad i = 1, \dots, p$

- $\log f_i(e^y)$ are (smooth) **convex** functions
- $\log g_i(e^y)$ are affine functions, *i.e.*, linear plus a constant
- solve (nonlinear) convex optimization problem above using interior-point method

Current state of the art

- basic interior-point method that exploits sparsity, generic GP structure
- approaching efficiency of linear programming solver
 - sparse 1000 vbles, 10000 monomial terms: few seconds
 - sparse 10000 vbles, 100000 monomial terms: minute
 - sparse 10^6 vbles, 10^7 monomial terms: hour

(these are order-of-magnitude estimates, on simple PC)

History

- GP (and term 'posynomial') introduced in 1967 by Duffin, Peterson,
 Zener
- engineering applications from the very beginning
 - early applications in chemical, mechanical, power engineering
 - digital circuit transistor and wire sizing with Elmore delay since 1984 (Fishburn & Dunlap's TILOS)
 - analog circuit design since 1997 (Hershenson, Boyd, Lee)
 - other applications in finance, wireless power control, statistics, . . .
- extremely efficient solution methods since 1994 or so (Nesterov & Nemirovsky)

Mixed-integer geometric program

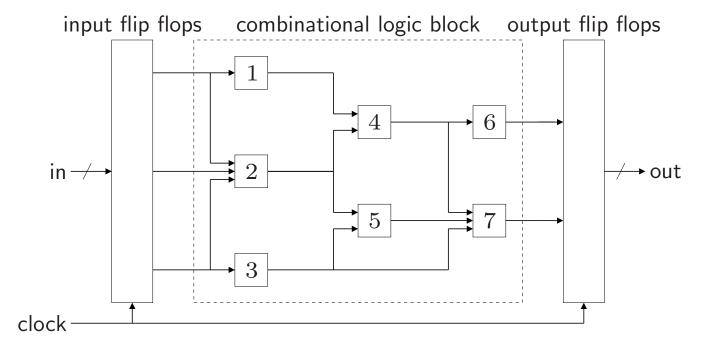
minimize
$$f_0(x)$$

subject to $f_i(x) \leq 1, \quad i = 1, \dots, m$
 $g_i(x) = 1, \quad i = 1, \dots, p$
 $x_i \in \mathcal{D}_i, \quad i = 1, \dots, k$

- f_i are generalized posynomials, g_i are monomials
- \mathcal{D}_i are discrete sets, e.g., $\{1,2,3,4,\ldots\}$ or $\{1,2,4,8\ldots\}$
- very hard to solve exactly; all methods make some compromise (compared to methods for GP)
- heuristic methods attempt to find good approximate solutions quickly, but cannot guarantee optimality
- global methods always find the global solution, but can be extremely slow

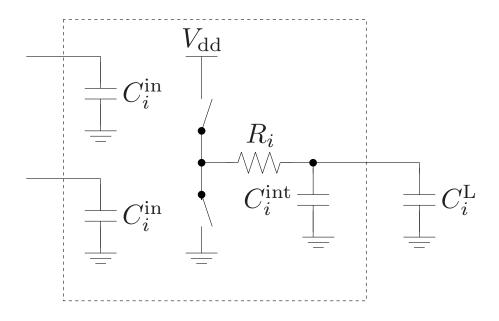
Digital Circuit Design Applications

Gate scaling



- combinational logic; circuit topology & gate types given
- gate sizes (scale factors $x_i \ge 1$) to be determined
- scale factors affect total circuit area, power and delay

RC gate delay model



• input & intrinsic capacitances, driving resistance, load capacitance

$$C_i^{\text{in}} = \bar{C}_i^{\text{in}} x_i, \qquad C_i^{\text{int}} = \bar{C}_i^{\text{int}} x_i, \qquad R_i = \bar{R}_i / x_i, \qquad C_i^{\text{L}} = \sum_{j \in \text{FO}(i)} C_j^{\text{in}}$$

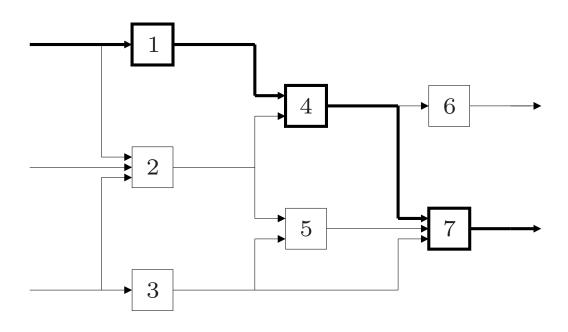
RC gate model

• RC gate delay:

$$D_{i} = 0.69R_{i}(C_{i}^{L} + C_{i}^{int}) = 0.69 \left(\bar{R}_{i}\bar{C}_{i}^{in} + (\bar{R}_{i}/x_{i}) \sum_{j \in FO(i)} \bar{C}_{j}^{in}x_{j} \right)$$

• D_i are **posynomials** (of scale factors)

Path and circuit delay



- delay of a path: sum of delays of gates on path
 - . . . posynomial
- circuit delay: maximum delay over all paths
 - ... generalized posynomial

Area & power

- total circuit area: $A = x_1 \bar{A}_1 + \cdots + x_n \bar{A}_n$
- total power is $P = P_{\rm dyn} + P_{\rm stat}$
 - dynamic power $P_{\mathrm{dyn}} = \sum_{i=1}^n f_i (C_i^{\mathrm{L}} + C_i^{\mathrm{int}}) V_{\mathrm{dd}}^2$

 f_i is gate switching frequency

- static power $P_{\text{stat}} = \sum_{i=1}^{n} x_i \bar{I}_i^{\text{leak}} V_{\text{dd}}$

 $ar{I}_i^{
m leak}$ is leakage current (average over input states) of unit scaled gate

ullet A and P are linear functions of x, with positive coefficients, hence posynomials

Basic gate scaling problem

$$\begin{array}{ll} \text{minimize} & D \\ \text{subject to} & P \leq P^{\max}, \quad A \leq A^{\max} \\ & 1 \leq x_i, \quad i = 1, \dots, n \end{array}$$

. . . a **GGP**

extensions/variations:

- minimize area, power, or some combination
- maximize clock frequency subject to area, power limits
- add other constraints
- optimal trade-off of area, power, delay

Clock frequency maximization

- $f_{\rm clk}$ is variable
- timing requirement: $D \le 0.8/f_{\rm clk}$ (20% margin for flip-flop delay, setup time, clock skew . . .)
- ullet P is posynomial of scalings and $f_{\rm clk}$, assuming f_i scale with $f_{\rm clk}$

maximize
$$f_{\rm clk}$$
 subject to $P \leq P^{\rm max}, \quad A \leq A^{\rm max}, \quad (1/0.8)Df_{\rm clk} \leq 1,$ $1 \leq x_i, \quad i=1,\ldots,n$

. . . a **GGP**

Example: 32-bit Ladner-Fisher adder

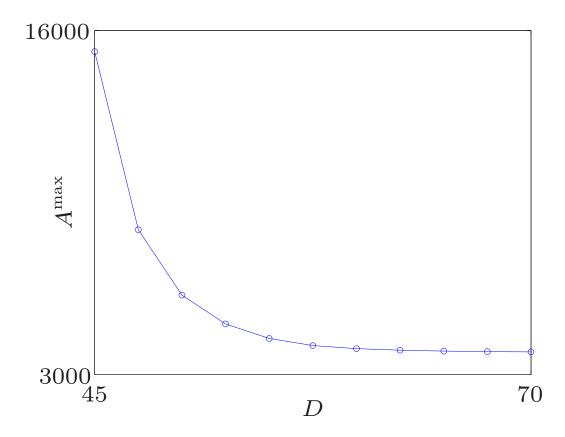
- 451 gates (scale factors), 5 gate types, 64 inputs, 32 outputs
- logical effort gate delay model parameters:

gate type	$ar{C}^{ ext{in}}$	$ar{C}^{\mathrm{int}}$	\bar{R}	$ar{A}$	$ar{I}^{ m leak}$
INV	3	3	0.48	3	0.006
NAND2	4	6	0.48	8	0.007
NOR2	5	6	0.48	10	0.009
AOI21	6	7	0.48	17	0.003
OAI21	6	7	0.48	16	0.003

- time unit is τ , delay of min-size inverter $(0.69 \cdot 0.48 \cdot 3 = 1)$
- area (total width) unit is width of NMOS in min-size inverter

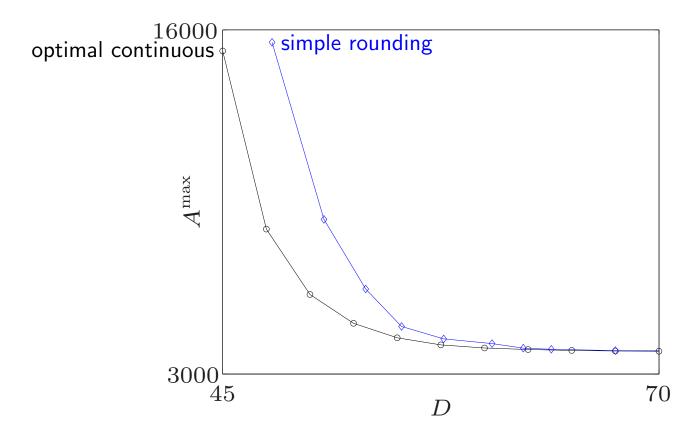
Example: 32-bit Ladner-Fisher adder

• typical optimization time: few seconds on PC



32-bit Ladner-Fisher adder with discrete scale factors

- add constraints $x_i \in \{1, 2, 4, 8, 16, \ldots\}$
- simple rounding of optimal continuous scalings



Sparse GP gate scaling problem

$$\begin{array}{ll} \text{minimize} & D \\ \text{subject to} & T_j \leq D \quad \text{for } j \text{ an output gate} \\ & T_j + D_i \leq T_i \quad \text{for } j \in \mathrm{FI}(i) \\ & P \leq P^{\max}, \quad A \leq A^{\max} \\ & 1 \leq x_i, \quad i = 1, \dots, n \end{array}$$

- \bullet T_i are upper bounds on signal arrival times
- extremely sparse GP; can be solved very efficiently

Better (generalized posynomial) models

can greatly improve model, while retaining GP compatibility (hence efficient global solution)

ullet area, delay, power can be any generalized posynomials of scale factors, e.g.,

$$D_i = a_i + b_i (C_i^{\mathrm{L}})^{1.05} x_i^{-0.9}, \qquad P_i = c_i + d_i (C_i^{\mathrm{L}})^{1.2} + e_i x_i^{1.1}$$

• these can be found by more refined analysis, or fitting generalized posynomials to simulation/characterization data

Distinguishing gate transitions

- can distinguish rising and falling transitions, with different delay, energy, $C^{\rm in}$, for each gate input/transition
- (bounds on) signal arrival times can be propagated through recursions,
 e.g.,

$$T_i^{\text{r}} = \max_{j \in \text{FI}(i)} \left\{ T_j^{\text{r}} + D_{ji}^{\text{rr}}, \ T_j^{\text{f}} + D_{ji}^{\text{fr}} \right\}, \quad T_i^{\text{f}} = \max_{j \in \text{FI}(i)} \left\{ T_j^{\text{r}} + D_{ji}^{\text{rf}}, \ T_j^{\text{f}} + D_{ji}^{\text{ff}} \right\}$$

 gate scaling problem more complex, but still a GGP (hence can be efficiently solved)

Modeling signal slopes

- ullet associate (worst-case) output signal transition time au with each gate
- model delay, energy, input capacitance as (generalized posynomial) functions of scale factor, load capacitance, input transition time
- propagate output transition time using (generalized posynomial)
 function of scale factor, load capacitance, input transition time
- common model:

$$D_i = a_i C_i^{\mathrm{L}} / x_i + \kappa_i \tau_i^{\mathrm{in}}, \qquad E_i = b_i (C_i^{\mathrm{L}} + c_i x_i) + \lambda_i x_i \tau_i^{\mathrm{in}}, \qquad \tau_i = \nu_i D_i$$

gate scaling problem still a GGP

Design with a standard library

- circuit topology is fixed; choose size for each gate from **discrete library**
- a combinatorial optimization problem, difficult to solve exactly

- GP approach
 - for each gate type in library, fit given library data to find GP-compatible models of delay, power, . . .
 - size with continuous fitted models, using GP
 - snap continuous scale factors back to standard library

Robust design over corners

- ullet have K corners or scenarios, e.g., combinations of
 - process parameters (channel length, oxide thickness, . . .)
 - environmental parameters (supply voltage, temperature, . . .)
- for each corner have (slightly) different models for delay, power, . . .
- robust design finds gate scalings that work well for all corners

Robust design over corners

• basic (worst-case) robust design over corners:

minimize
$$D^{\mathrm{wc}} = \max\{D^{(1)}, \dots, D^{(K)}\}$$

subject to $P^{(1)}(x) \leq P^{\mathrm{max}}, \dots, P^{(K)}(x) \leq P^{\mathrm{max}}$
 $A \leq A^{\mathrm{max}}$
 $1 \leq x_i, \quad i = 1, \dots, n$

ullet many variations, e.g., minimize average delay over corners,

$$D^{\text{avg}} = (1/K) \left(D^{(1)} + \dots + D^{(K)} \right)$$

• results in (very large, but sparse) **GGP**

Multiple-scenario design

- ullet have K scenarios or operating modes, with K models for P, D, \ldots
- scenarios are combinations of
 - supply & threshold voltages
 - clock frequency
 - specifications & constraints
- like corner-based robust design, but scenarios are intentional
- find one set of gate scalings that work well in all scenarios

Example

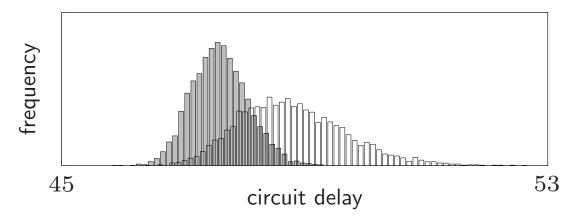
- find single set of gate scalings to support both high performance mode and low power mode
 - in high performance mode: $P^{\mathrm{fast}} \leq \bar{P}^{\mathrm{fast}}$, $D^{\mathrm{fast}} \leq \bar{D}^{\mathrm{fast}}$
 - in low power mode: $P^{\mathrm{slow}} \leq \bar{P}^{\mathrm{slow}}$, $D^{\mathrm{slow}} \leq \bar{D}^{\mathrm{slow}}$

minimize
$$A$$
 subject to $P^{\mathrm{slow}} \leq \bar{P}^{\mathrm{slow}}, \quad D^{\mathrm{slow}} \leq \bar{D}^{\mathrm{slow}}$ $P^{\mathrm{fast}} \leq \bar{P}^{\mathrm{fast}}, \quad D^{\mathrm{fast}} \leq \bar{D}^{\mathrm{fast}}$ $1 \leq x_i, \quad i = 1, \dots, n$

...a **GGP**

Statistical parameter variation

- circuit peformance depends on random device and process parameters
- ullet hence, performance measures like P, D are random variables ${\bf P}$, ${\bf D}$
- delay **D** is max of many random variables; often skewed to right
- distributions of P, D depend on gate scalings x_i



• related to (parametric) yield, DFM, DFY . . .

Statistical design

• measure random performance measures by 95% quantile (say)

minimize
$$\mathbf{Q}^{.95}(\mathbf{D})$$

subject to $\mathbf{Q}^{.95}(\mathbf{P}) \leq P^{\max}, \quad A \leq A^{\max}$
 $1 \leq x_i, \quad i = 1, \dots, n$

- extremely difficult stochastic optimization problem; almost no analytic/exact results
- but, (GP-compatible) heuristic method works well

Statistical model

- ullet for simplicity consider $V_{
 m th}$ variation only
- Pelgrom's model: $\sigma_{V_{\rm th}} = \bar{\sigma}_{V_{\rm th}} x^{-1/2}$
- alpha-power law model: $D \propto V_{\rm dd}/(V_{\rm dd}-V_{\rm th})^{\alpha}$, with $\alpha \approx 1.3$
- ullet for small variation in $V_{
 m th}$,

$$\sigma_D \approx \left| \frac{\partial D}{\partial V_{\rm th}} \right| \sigma_{V_{\rm th}} = \alpha (V_{\rm dd} - V_{\rm th})^{-1} \bar{\sigma}_{V_{\rm th}} x^{-0.5} D$$

- ullet σ_D is posynomial
- ullet get similar (posynomial) models for σ_D with more complex gate delay statistical models

Heuristic for statistical design

- ullet assume generalized posynomial models for gate delay mean $D_i(x)$ and variance $\sigma_i(x)^2$
- optimize using surrogate gate delays

$$\tilde{D}_i(x) = D_i(x) + \kappa_i \sigma_i(x)$$

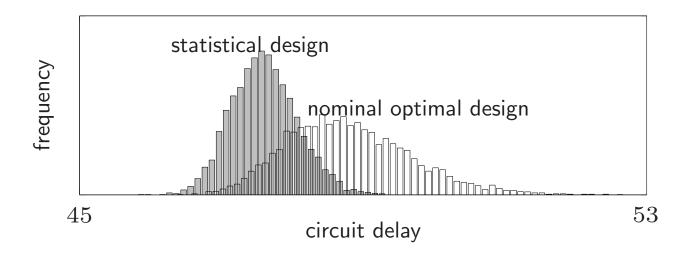
 $\kappa_i \sigma_i(x)$ are **margins** on gate delays (κ_i is typically 2 or 3)

• verify statistical performance via Monte Carlo analysis (can update κ_i 's and repeat)

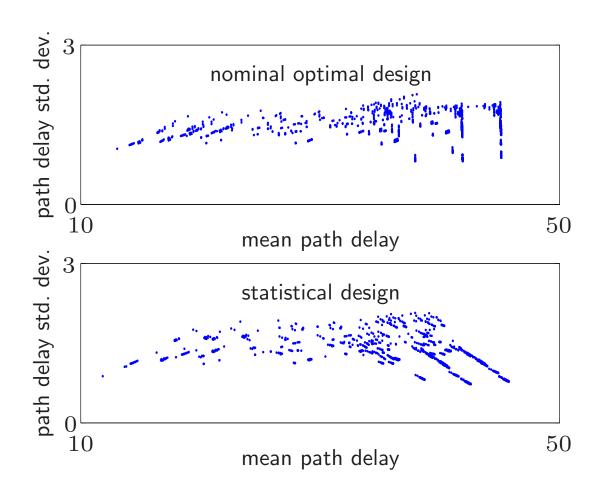
Heuristic for statistical design

heuristic statistical design

- often far superior to design obtained ignoring statistical variation
- not very sensitive to details of process variation statistics (distribution shape, correlations, . . .)
- below: 32-bit Ladner-Fisher adder, Pelgrom variance model



Path delay mean/std. dev. scatter plots



Joint size and supply/threshold voltage optimization

- goal: jointly optimize gate size, supply and threshold voltages via GGP
- **need to:** model delay, power as generalized posynomial functions of gate size, supply and threshold voltages

Generalized posynomial delay model

ullet alpha-power law model predicts variation in gate delay with $V_{
m dd}$, $V_{
m th}$:

$$D_i = \frac{V_{\mathrm{dd},i}}{(V_{\mathrm{dd},i} - V_{\mathrm{th},i})^{\alpha}} \tilde{D}_i(x)$$

 $ilde{D}_i$ is generalized posynomial gate delay model, function of scalings x

generalized posynomial approximation

$$\widehat{D}_i = V_{\mathrm{dd},i}^{1-\alpha} (1 + V_{\mathrm{th},i}/V_{\mathrm{dd},i} + \dots + (V_{\mathrm{th},i}/V_{\mathrm{dd},i})^5)^{\alpha} \widetilde{D}_i(x)$$

error under 1% for $V_{\mathrm{dd},i} \geq 2V_{\mathrm{th},i}$, $1.3 \leq \alpha \leq 2$

Generalized posynomial power model

• gate dynamic power:
$$P_{\mathrm{dyn}} = \sum_{i=1}^n f_i (C_i^{\mathrm{L}} + C_i^{\mathrm{int}}) V_{\mathrm{dd},i}^2$$

• simple static power model:

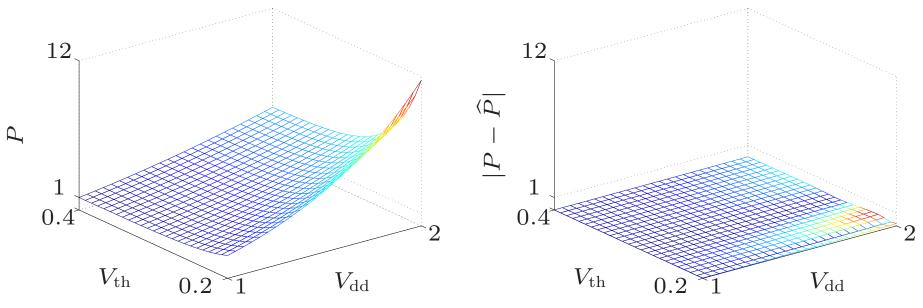
$$P_{\text{stat}} = \sum_{i=1}^{n} x_i \bar{I}_i^{\text{leak}} V_{\text{dd},i}, \qquad \bar{I}_i^{\text{leak}} \propto e^{-(V_{\text{th},i} - \gamma V_{\text{dd},i})/V_0}$$

 γ , V_0 are (process) constants

- $P_{\rm stat}$ (by itself) **cannot** be approximated well by a generalized posynomial over large range of $V_{\rm dd}$, $V_{\rm th}$
- but, total power $P = P_{\rm dyn} + P_{\rm stat}$ can be approximated well by a generalized posynomial

Generalized posynomial power model example

total power $P = V_{\rm dd}^2 + 30 V_{\rm dd} e^{-(V_{\rm th} - 0.06 V_{\rm dd})/0.039}$ (up to scaling)



- generalized posynomial approximation $\widehat{P} = V_{\rm dd}^2 + 0.06 V_{\rm dd} (1 + 0.0031 V_{\rm dd})^{500} (V_{\rm th}/0.039)^{-6.16}$
- error under 3% (well under accuracy of model!)

Joint optimization of gate sizes, V_{dd} , & V_{th}

basic problem, with variables: x_i , $V_{\mathrm{th},i}$, $V_{\mathrm{dd},i}$

```
minimize D subject to P \leq P^{\max}, \quad A \leq A^{\max} V_{\mathrm{th}}^{\min} \leq V_{\mathrm{th},i} \leq V_{\mathrm{th}}^{\max}, \quad i = 1, \dots, n V_{\mathrm{dd}}^{\min} \leq V_{\mathrm{dd},i} \leq V_{\mathrm{dd}}^{\max}, \quad i = 1, \dots, n other constraints . . .
```

(... a **GGP**)

discrete allowed V_{dd} , V_{th} values yields MIGP

Extensions/variations

• clustering, with single $V_{\rm dd}$, $V_{\rm th}$ per cluster:

$$V_{\mathrm{dd},i} = V_{\mathrm{dd},j}, \quad V_{\mathrm{th},i} = V_{\mathrm{th},j} \quad \text{for } i,j \text{ in same cluster}$$

- . . . monomial (equality) constraints
- ullet clustered voltage scaling (CVS): low $V_{
 m dd}$ cells cannot drive high $V_{
 m dd}$ cells

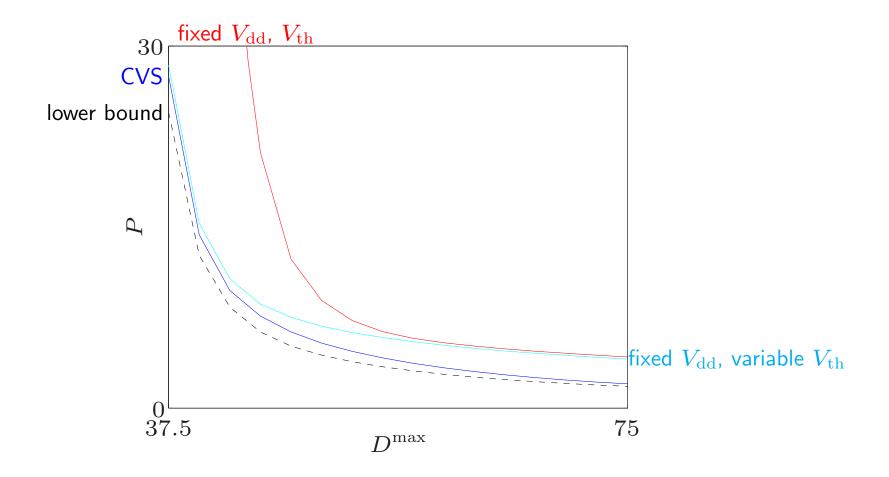
$$V_{\mathrm{dd},j} \leq V_{\mathrm{dd},i} \quad \text{for } j \in \mathrm{FO}(i)$$

- . . . monomial (inequality) constraints
- \bullet multimode design: choose single set of gate scalings, different $V_{\rm dd}^{(k)}$, $V_{\rm th}^{(k)}$ for each scenario $k=1,\ldots,K$
 - related to dynamic voltage scaling, adaptive bulk biasing, . . .

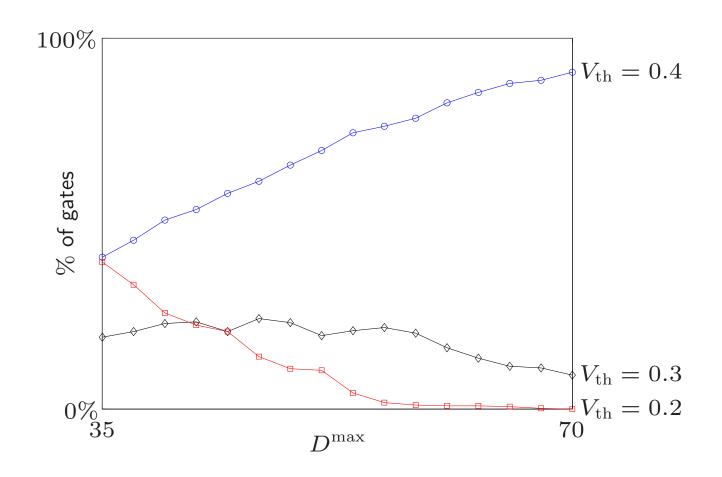
Joint optimization examples

- Ladner-Fisher adder
- variables: gate scalings x_i , supply voltages $V_{\mathrm{dd},i}$, threshold voltages $V_{\mathrm{th},i}$
- four delay-power trade-off curves:
 - fixed $V_{\mathrm{dd},i} = 1.0$, fixed $V_{\mathrm{th},i} = 0.3$
 - fixed $V_{\mathrm{dd},i} = 1.0$, variable $V_{\mathrm{th},i} \in \{0.2, 0.3, 0.4\}$
 - CVS with $V_{\mathrm{dd},i} \in \{0.6, 1.0\}, V_{\mathrm{th},i} \in \{0.2, 0.3, 0.4\}$
 - variable continuous $V_{\rm dd}$, $V_{\rm th}$, $0.6 \le V_{{\rm dd},i} \le 1.0$, $0.2 \le V_{{\rm th},i} \le 0.4$ (not practical, but serves as lower bound)

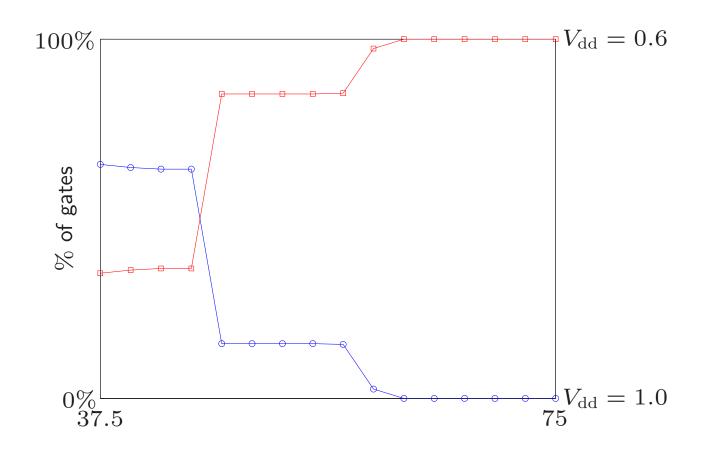
Trade-off curve analysis



Design with multiple threshold voltages

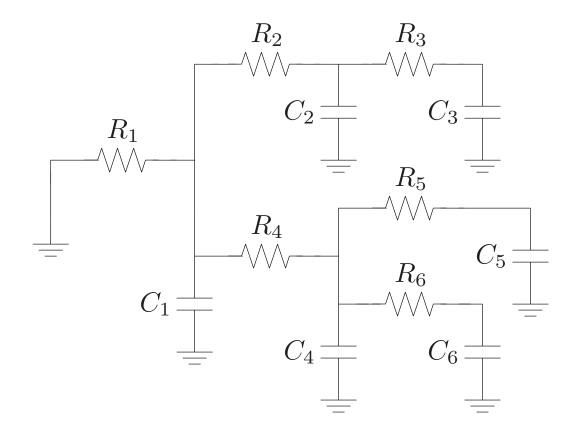


Clustered voltage scaling



Wire and device sizing

RC tree:



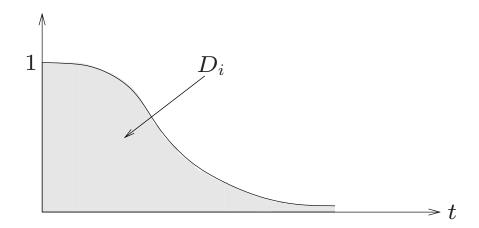
• R_i s and C_i s are generalized posynomials of some underlying variables x

Elmore delay

• **Elmore delay** at node *i*:

$$D_i = \int_0^\infty v_i(t) \ dt$$

area under voltage curve, when voltages are initialized as $v_i(0)=1$



• Elmore delay of RC tree is $D = \max\{D_1, \dots, D_N\}$

Elmore delay expression

ullet analytic expression for Elmore delay D_i

$$D_i = \sum_{j \in \mathbf{P}(i)} R_i C_i^{\text{tot}}$$

- P(i) is path from root to node i
- C_i^{tot} is the total capacitance downstream from node i (including C_i)
- D_i is **posynomial** of x
- ullet D is **generalized posynomial** of x

RC tree optimization

• minimize RC tree delay subject to (generalized posynomial) constraints

minimize
$$D$$
 subject to $f_i(x) \leq 0, \quad i = 1, \dots, m$

...a **GGP**

• sparse formulation:

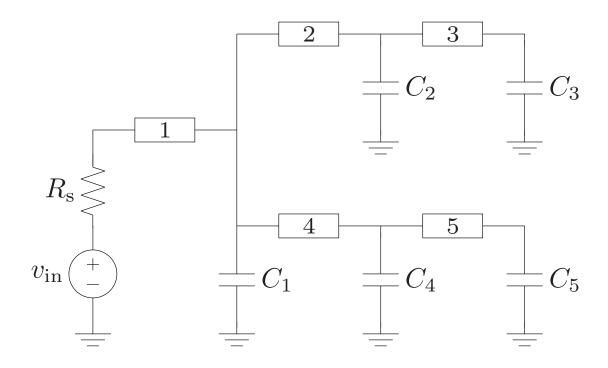
minimize
$$s$$
 subject to $s \geq D_i, \quad i = 1, \dots, n$
$$C_j^{\text{tot}} \geq \sum_{i \in \mathbf{Child}(j)} C_i^{\text{tot}} + C_j, \quad i = 1, \dots, n$$

$$D_i \geq D_{\mathbf{Par}(k)} + R_i C_i^{\text{tot}}, \quad i = 1, \dots, n$$

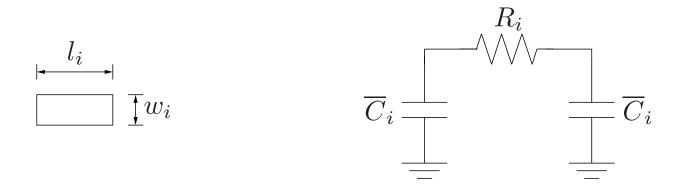
$$f_i(x) \leq 0, \quad i = 1, \dots, m$$

Wire sizing

- ullet choose wire segment widths w_i,\ldots,w_N in an interconnect network
- optimize delay, area



π model for wire segment



• wire resistance and capacitances

$$R_i = \alpha_i \frac{l_i}{w_i}, \qquad \overline{C}_i = \beta_i l_i w_i + \gamma_i l_i,$$

ullet with π model, interconnect network becomes RC tree, with R_i s and C_i s posynomial functions of wire segment widths w_i

Wire sizing via GP

minimize
$$D$$
 subject to $w_i^{\min} \leq w_i \leq w_i^{\max}, \quad i=1,\ldots,N$ $l_1w_1+\cdots+l_Nw_N \leq A^{\max}$

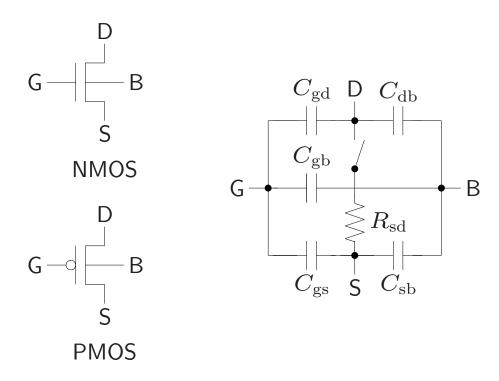
...a **GGP**

- \bullet can easily optimize interconnect network with 10000 wires, using sparse GP formulation
- ullet can use more accurate generalized posynomial models of R_i , C_i

Device sizing

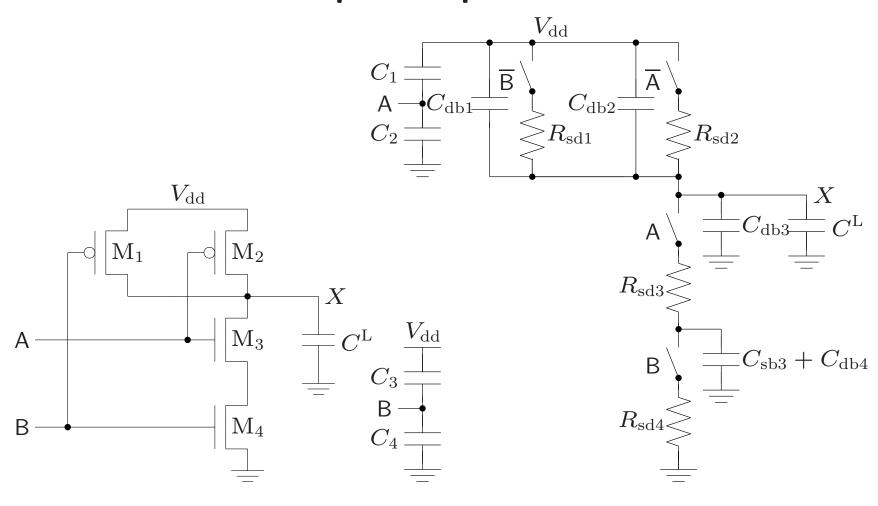
- devices (and wire segments) are sized individually
- replace each device with switch-level RC model
- each transition is associated with RC tree
- use Elmore delay to measure delay of transition
- ... problem is GGP

Switch-level RC device model



- crude linear approximation of device, for delay and power optimization
- R, all Cs are generalized posynomials of device width
- ullet we'll ignore $C_{
 m gd}$ (but can be incorporated via Miller effect . . .)

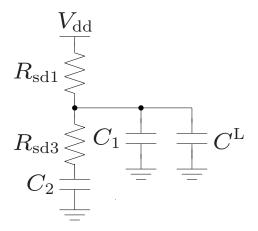
Example: 2-input NAND



$$C_1 = C_{\text{gb2}} + C_{\text{gs2}}, \quad C_2 = C_{\text{gb3}} + C_{\text{gs3}}, \quad C_3 = C_{\text{gb1}} + C_{\text{gs1}}, \quad C_4 = C_{\text{gb4}} + C_{\text{gs4}}$$

Example transition

- ullet transition: B falls from $V_{
 m dd}$ to zero; A remains at $V_{
 m dd}$
- associated RC tree:

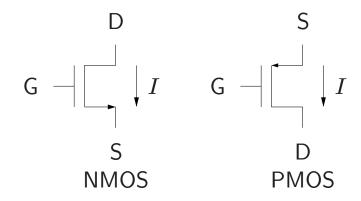


$$C_1 = C_{\text{db1}} + C_{\text{db2}} + C_{\text{db3}}, C_2 = C_{\text{sb3}} + C_{\text{db4}}$$

- Elmore delay: $D = R_{\rm sd1}(C^{\rm L} + C_1 + C_2)$
- ullet energy lost: $E=(C^{\mathrm{L}}+C_1+C_2)V_{\mathrm{dd}}^2/2$

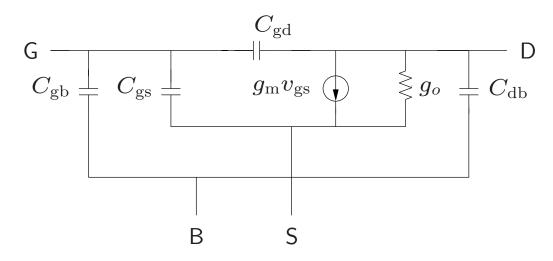
Analog and RF Circuit Design Applications

Large signal MOS model



- ullet gate overdrive voltage $V_{
 m gov} = V_{
 m gs} V_{
 m th}$
- saturation condition: $V_{\rm ds} \geq V_{\rm dsat} = V_{\rm gov} \ (V_{\rm dsat} \ {\rm is \ minimum} \ {\rm drain}$ -source voltage for device to operate in saturation)
- square-law model $I=0.5\mu C_{\rm ox}(W/L)V_{\rm gov}^2$
- GP model variables: I, L, W
- $V_{\rm gov} = (\mu C_{\rm ox}/2)^{-1/2} I^{1/2} L^{1/2} W^{-1/2}$ is monomial
- ullet $V_{
 m gs} = V_{
 m gov} + V_{
 m th}$ is posynomial

Small signal dynamic MOS model



- \bullet transconductance $g_{\rm m}=(2\mu C_{\rm ox})^{1/2}I^{1/2}L^{-1/2}W^{1/2}$ is monomial
- ullet output conductance $g_{\mathrm{o}}=\lambda I$ is monomial
- ullet all capacitances are (approximately) posynomial in $I,\ L,\ W$
- better (GP-compatible) models can be obtained by fitting data from accurate models or measurements

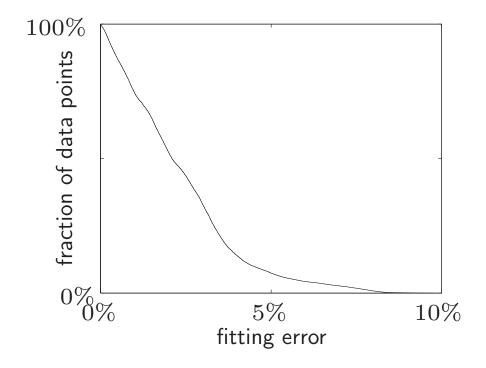
Example: monomial $g_{\rm m}$ model

- ullet monomial model of $g_{
 m m}$ for I/O NMOS device in a $0.13 \mu {
 m m}$ technology
- 11000 data points (from BSIM3) over ranges
 - $-0.3\mu\mathrm{m} \le L \le 3\mu\mathrm{m}, \quad 2\mu\mathrm{m} \le W \le 20\mu\mathrm{m}$
 - $-0.7V \le V_{\rm gs} \le 1.7V$, $V_{\rm dsat} \le V_{\rm ds} \le 1.5V_{\rm gs}$
- ullet $V_{
 m ds}$ appears in data set, but not in $g_{
 m m}$ model
- monomial fit (using simple log-regression, SI units):

$$g_{\rm m} = 0.0278I^{0.4798}L^{-0.511}W^{0.5632}$$

Example: monomial $g_{\rm m}$ model

• fitting (relative) error cumulative distribution plot:

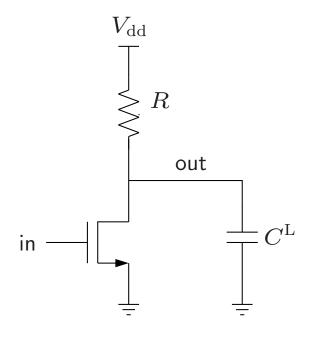


 \bullet for 90% of points, fit is better than 4%

Single transistor common source amplifier

- \bullet variables: I, L, W, R
- saturation: $V_{\rm dsat} + IR \le V_{\rm dd}$
- gain $G = g_{\rm m}/(1/R + g_{\rm o})$
- power $P = V_{\mathrm{dd}}I$
- ullet (unity gain) bandwidth $B=g_{
 m m}/C^{
 m L}$
- design problem:

$$\begin{array}{ll} \text{minimize} & P \\ \text{subject to} & B \geq B^{\min}, \quad G \geq G^{\min} \\ & \text{saturation} \end{array}$$



Common source amplifier design via GP

rewrite as

minimize
$$P$$
 subject to $B^{-1} \leq 1/B^{\min}, \quad G^{-1} \leq 1/G^{\min}$ $V_{\rm dsat} + IR \leq V_{\rm dd}$

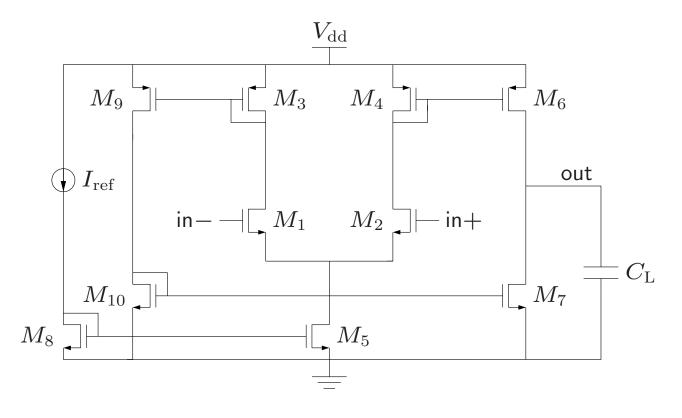
ullet . . . a **GP**, since P and B are monomials, and

$$G^{-1} = \frac{1/R + g_{\rm o}}{g_{\rm m}}$$

is posynomial

• this is a simple problem; don't need GP sledgehammer . . .

Current mirror opamp



- M_1, M_2 and M_3, M_4 matched pairs
- four current mirrors: M_8, M_5 ; M_{10}, M_7 ; M_9, M_3 ; M_4, M_6

Design problem

$$\begin{array}{ll} \text{minimize} & P \\ \text{subject to} & B \geq B^{\min}, \quad G \geq G^{\min}, \quad A \leq A^{\max} \\ & \text{other constraints . . .} \end{array}$$

- objective & specifications:
 - P is power dissipation
 - $-\ B$ is unity gain bandwidth
 - -G is DC gain
 - -A is (active) area
- design variables: $L_1, \ldots, L_{10}, W_1, \ldots, W_{10}$
- ullet given: $V_{
 m dd}$, $C_{
 m L}$, $I_{
 m ref}$, common-mode voltage $V_{
 m cm}$
- we'll formulate as GP

Power, bandwidth, gain, & area

• power:
$$P = V_{\rm dd}(I_8 + I_5 + I_7 + I_{10})$$
 ... posynomial

$$ullet$$
 bandwidth: $B=g_{
m m,2}g_{
m m,6}/(g_{
m m,4}C_{
m L})$

$$ullet$$
 area: $A=W_1L_1+\cdots+W_{10}L_{10}$

$$ullet$$
 gain: $G = rac{g_{
m m,2}g_{
m m,6}}{g_{
m m,4}(g_{
m o,6}+g_{
m o,7})}$

... G^{-1} is posynomial, so $G \geq G^{\min}$ can be written as $G^{-1} \leq 1/G^{\min}$

Dimension, matching, and current constraints

- limits on device sizes: $L_{\min} \leq L_i \leq L_{\max}$, $W_{\min} \leq W_i$, $i = 1, \ldots, 10$
- differential symmetry constraints $(M_1, M_2 \text{ and } M_3, M_4 \text{ matched})$:

$$W_1 = W_2,$$
 $L_1 = L_2,$ $I_1 = I_2,$ $W_3 = W_4,$ $L_3 = L_4,$ $I_3 = I_4,$

• length & gate overdrive voltage matched for current mirror pairs:

$$L_5 = L_8,$$
 $L_{10} = L_7,$ $L_3 = L_9,$ $L_4 = L_6$ $V_{\text{gov},5} = V_{\text{gov},8},$ $V_{\text{gov},10} = V_{\text{gov},7},$ $V_{\text{gov},3} = V_{\text{gov},9},$ $V_{\text{gov},4} = V_{\text{gov},6}$

current relations:

$$I_1 = I_3 = I_5/2$$
, $I_8 = I_{ref}$, $I_6 = I_7$, $I_9 = I_{10}$

Saturation constraints

- diode connected devices (M_3, M_4, M_8, M_{10}) automatically in saturation
- others must have $V_{\rm ds} \geq V_{\rm dsat}$:
 - $-M_7$: $V_{\text{dsat},7} \leq V_{\text{cm}}$
 - M_6 : $V_{\text{dsat},6} + V_{\text{cm}} \leq V_{\text{dd}}$
 - M_9 : $V_{\text{dsat},9} + V_{\text{gs},10} \le V_{\text{dd}}$
 - M_5 : $V_{ds,5} + V_{gs,1} \le V_{cm}$
 - $M_1 \& M_2$: $V_{\rm cm} + V_{\rm gs,3} \le V_{\rm dd} + V_{\rm th}$
- . . . all are posynomial inequalities

Node capacitances and non-dominant poles

capacitances at nodes are posynomials, e.g.,

$$C^{\text{out}} = C_{\text{gd},6} + C_{\text{db},6} + C_{\text{gd},7} + C_{\text{db},7} + C_{\text{L}}$$

• non-dominant time constants are posynomials:

$$\tau_1 = \frac{C_{d1}}{g_{m,3}}, \qquad \tau_2 = \frac{C_{d2}}{g_{m,4}}, \qquad \tau_9 = \frac{C_{d9}}{g_{m,10}}$$

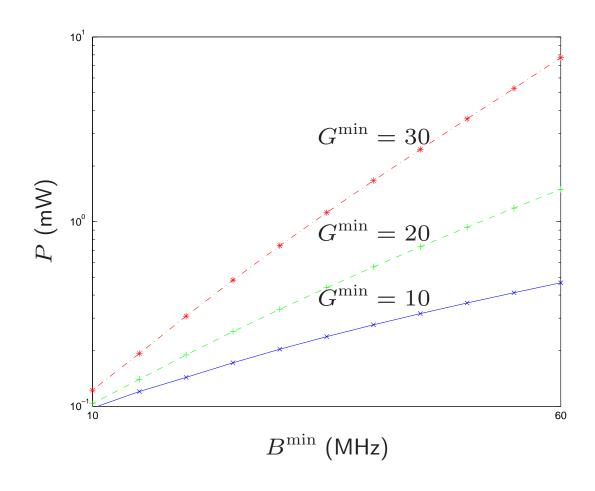
 (C_{d1}, C_{d2}, C_{d9}) are node capacitances at drains of M_1, M_2, M_9

• to limit effect of non-dominant poles, make sum smaller than dominant time constant:

$$\tau_1 + \tau_2 + \tau_9 \le \tau_{\text{dom}} = C_{\text{L}}/g_{\text{m}}$$

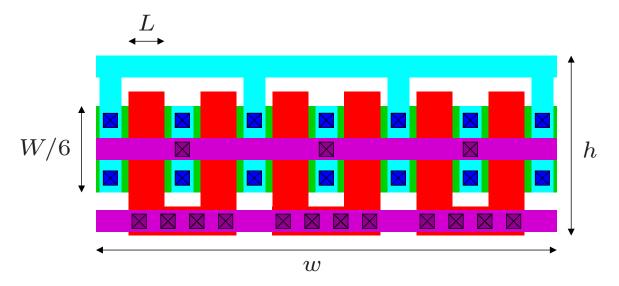
. . . a posynomial constraint

Power versus bandwidth trade-off



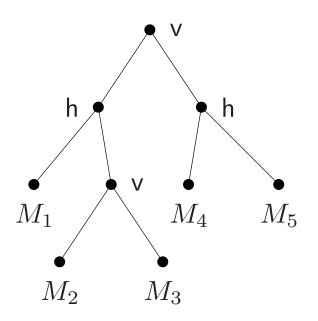
Joint electrical/physical design

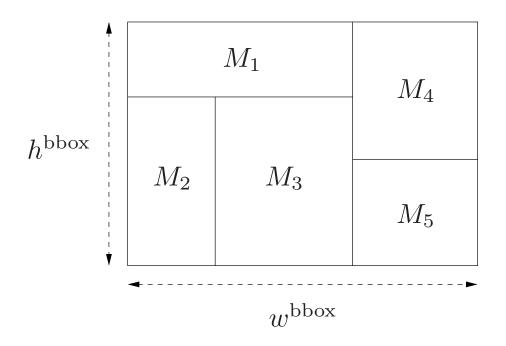
- ullet each device has a (physical) cell width w and height h for floor planning
- devices are folded into multiple fingers
- (approximate) posynomial or monomial relations link electrical variables (I, L, W) and physical variables (w, h), e.g.
 - cell area is at least $4\times$ active area: $wh \geq 4WL$
 - cell aspect ratio limited to 5:1: $1/5 \le w/h \le 5$



Slicing tree layout scheme

- vertical and horizontal slices fix relative placement of device cells
- leaves are device cells; root is bounding box





Slicing tree constraints

- introduce width, height for each node in slicing tree
- ullet for each vertical slice with parent a and children b,c add constraints

$$w_a = w_b + w_c, \qquad h_a = \max\{h_b, h_c\}$$

ullet for each horizontal slice with parent a and children b,c add constraints

$$w_a = \max\{w_b, w_c\}, \qquad h_a = h_b + h_c$$

- shows width and height of bounding box and each node is generalized posynomial of device cell widths, heights
- resulting GP formulation is very sparse

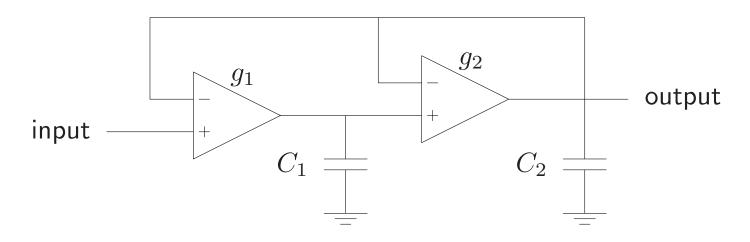
Joint electrical/physical design via GP

- form **one** GP that includes
 - electrical variables, constraints $(I_i, L_i, W_i, g_{\mathrm{m},i} \dots)$
 - physical variables, constraints $(w_i, h_i, w^{\text{bbox}}, h^{\text{bbox}}, \dots)$
 - coupling constraints $(w_i h_i \geq 4W_i L_i, \dots)$
- solve it all together

- extensions: can add
 - parasitic estimates
 - more accurate expressions for device cell dimensions
 - channels for routing

Optimal filter implementation

simple Gm-C two-pole lowpass filter



transfer function is

$$H(s) = \frac{1}{1 + t_1 s + t_1 t_2 s^2}, t_1 = C_1/g_1, t_2 = C_2/g_2$$

 g_i is amplifier transconductance

Noise analysis

- \bullet N_i is input referred (white) amplifier input-referred voltage density
- spectral density of output noise is

$$N(\omega)^2 = \frac{N_1^2 + \omega^2 N_2^2}{(1 - t_1 t_2 \omega^2)^2 + t_1^2 \omega^2}$$

• root-mean-square output noise voltage is

$$M = \left(\int_0^\infty N(\omega)^2 \, d\omega\right)^{1/2} = \left(\alpha N_1^2 + \beta N_2^2\right)^{1/2}$$

Amplifier and capacitor implementation models

- each amplifier has **private variables** u (e.g., device lengths & widths) and constraints
- ullet transconductance g is monomial in u; area A^{amp} , power P, input-referred noise density N are posynomial in u
- ullet each capacitor has private variables v (e.g., physical dimensions) and constraints
- capacitance C is monomial in v; area A^{cap} is posynomial
- design variables are u_1 , u_2 , v_1 , v_2

Optimal filter implementation problem

• filter is Butterworth with frequency ω_c :

$$t_1 = \sqrt{2}/\omega_c, \qquad t_2 = (1/\sqrt{2})/\omega_c$$

 minimize total power of implementation, subject to area, output noise limits:

minimize
$$\begin{split} P(u_1) + P(u_2) \\ \text{subject to} \quad t_1 &= \sqrt{2}/\omega_c, \quad t_2 = (1/\sqrt{2})/\omega_c \\ \quad A^{\text{amp}}(u_1) + A^{\text{amp}}(u_2) + A^{\text{cap}}(v_1) + A^{\text{cap}}(v_2) \leq A^{\text{max}} \\ \quad M &= (\omega_c/4\sqrt{2})(N_1^2 + 2N_2^2)^{1/2} \leq M^{\text{max}} \end{split}$$

ullet a **GGP** in the variables u_1 , u_2 , v_1 , v_2

Example

- Butterworth filter with $\omega_c = 10^8 \mathrm{rad/s}$
- ullet private variables in amplifiers: (equivalent) L, W
- amplifier model:

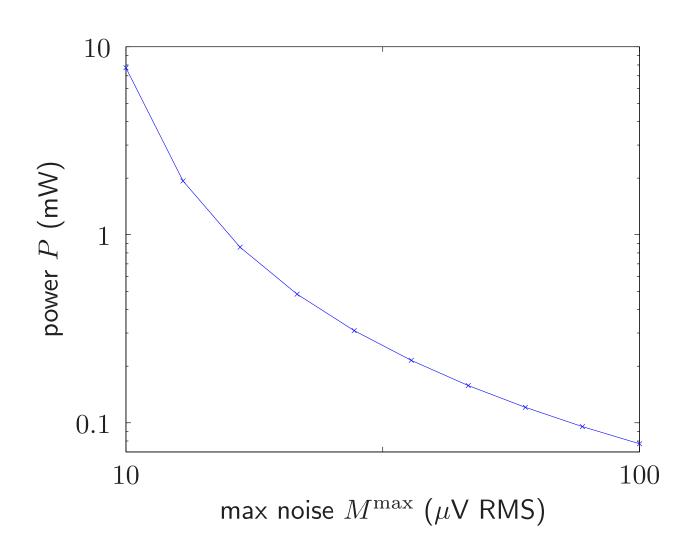
$$A^{\text{amp}} = WL, \qquad P = 2.5 \cdot 10^{-4} W/L,$$

 $g = 4 \cdot 10^{-5} W/L, \qquad N = \sqrt{7.5 \cdot 10^{-16} L/W}$

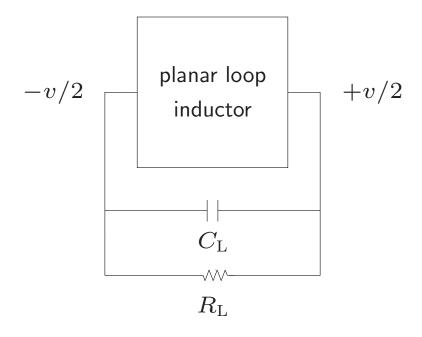
(based on simple model with $V_{\rm dd}=2.5$, $V_{\rm gov}=0.2$)

- private variable in capacitors is area $A^{\rm cap}$; $C=10^{-4}A^{\rm cap}$
- $A^{\text{max}} = 4 \cdot 10^{-6}$

Power versus noise trade-off



Spiral inductor/differential resonator optimization



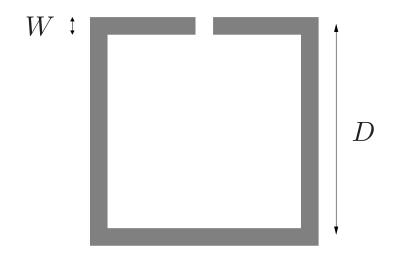
- ullet loop inductor connected to (given) $R_{
 m L}$ and $C_{
 m L}$
- differential (floating) mode operation
- ullet inductor designed to resonate at operating frequency f

Design problem: differential resonator

maximize
$$R_{\rm T}$$
 subject to $Q_{\rm T} \geq Q_{\rm T}^{\rm min}, \quad A \leq A^{\rm max}$ other constraints . . .

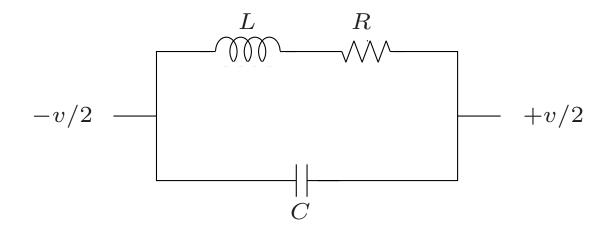
- objective & specifications:
 - $-R_{\rm T}$ is tank impedance (which is real at operating frequency f)
 - Q_{T} is tank quality factor
 - -A is area of loop inductor
- design variables: dimensions of loop inductor
- load resistance $R_{\rm L}$, load capacitance $C_{\rm L}$, frequency f given
- we'll formulate as GP

Loop inductor



- ullet (centerline) diameter D
- $\bullet \ \ \mathsf{width} \ W$
- ullet outer diameter is D+W; area is $A=(D+W)^2$

Lumped model for loop inductor



- lumped model for operation in differential mode
- ullet impact of substrate capacitance, loss included in R and C

Example

- $\bullet \ \ \text{frequency range} \ 2 \text{GHz} \leq f \leq 6 \text{GHz}$
- metal layer thickness 2μ m, resistivity $5 \cdot 10^{-8} \Omega$ m
- \bullet metal-substrate capacitance density $5 \cdot 10^{-6} \mathrm{Fm}^2$
- width, diameter constraints:

$$150 \mu \text{m} \le D \le 600 \mu \text{m}, \quad 4 \mu \text{m} \le W \le 30 \mu \text{m}, \quad 10 \le D/W \le 100$$

GP models for L, R and C

- can get exact values via EM simulation
- inductance (monomial)

$$L = 2.1 \cdot 10^{-6} D^{1.28} W^{-0.25} f^{-0.01}$$

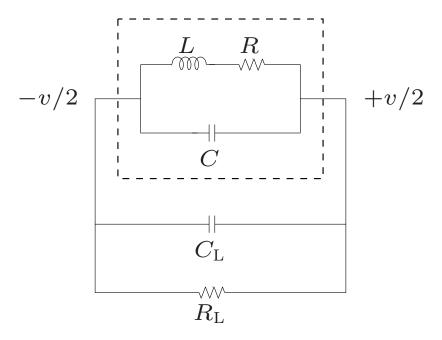
resistance (posynomial)

$$R = 0.1DW^{-1} + 3.10^{-6}DW^{-0.84}f^{0.5} + 5.10^{-9}DW^{-0.76}f^{0.75} + 0.02DWf$$

• capacitance (posynomial):

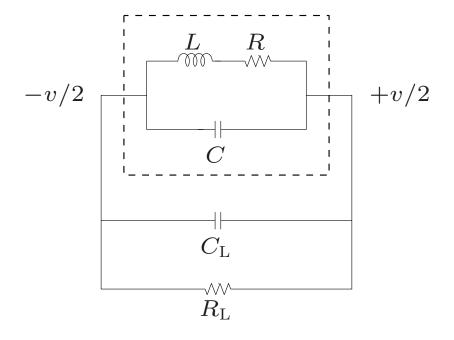
$$C = 5 \cdot 10^{-6} DW + 1 \cdot 10^{-11} D$$

Resonance constraint



- resonance condition: $4\pi^2 f^2 L C_{\rm T} = 1 \ (C_{\rm T} = C + C_{\rm L})$
- to handle in GP:
 - impose posynomial constraint $C + C_{\rm L} \leq C_{\rm T}$
 - add extra capacitance (after design) $C_{
 m extra} = C_{
 m T} C C_{
 m L}$ if needed

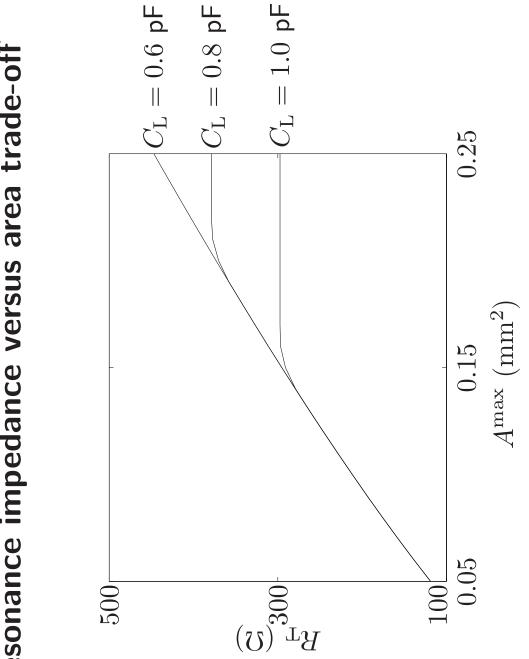
Tank conductance and quality factor



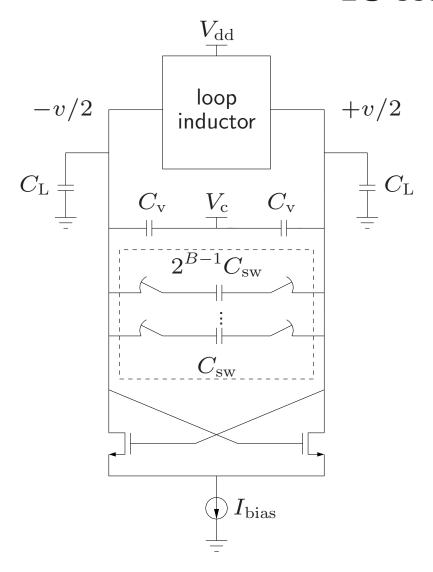
$$\bullet$$
 tank conductance: $G_{\rm T}=\frac{1}{R_{\rm T}}=\frac{R}{4\pi^2f^2L^2}+\frac{1}{R_{\rm L}}$. . . posynomial

$$\bullet$$
 inverse of tank quality factor: $\frac{1}{Q_{\rm T}} = \frac{R}{2\pi f L} + \frac{2\pi f L}{R_{\rm L}}$. . . posynomial

Resonance impedance versus area trade-off



LC oscillator



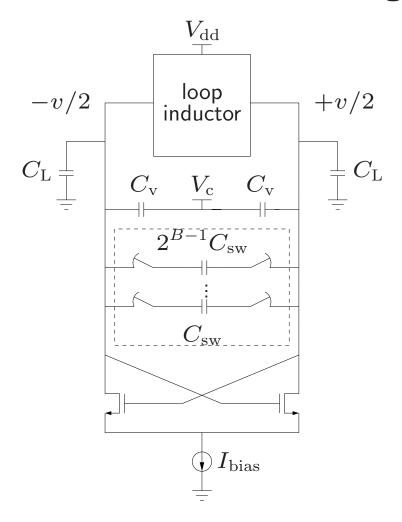
- loop inductor
- varactors for fine tuning
- binary weighted switching capacitors for coarse tuning
- cross coupled NMOS transistors
- tail current source

LC oscillator design problem

 $\begin{array}{ll} \text{minimize} & P \\ \text{subject to} & N \leq N^{\max}, \quad A \leq A^{\max}, \quad l \geq l^{\min} \\ & \text{other constraints} \dots \end{array}$

- objective & specifications:
 - P is power consumption
 - -N is phase noise
 - -A is area of loop inductor
 - -l is loop gain
- ullet given: load capacitance $C_{\rm L}$, center frequency f, normalized tuning range T
- we'll formulate as GP

Design variables



- ullet loop inductor dimensions D, W
- ullet size of varactor $V_{
 m c}$
- ullet size of switching capacitors $C_{
 m sw}$
- ullet width, length of transistors $W_{
 m nmos}$, $L_{
 m nmos}$
- bias current $I_{\rm bias}$

Current source, switched capacitor, and varactor models

- ullet $I_{
 m bias}$ is bias current, with minimum operating voltage $V_{
 m bias}$
- binary weighted capacitors
 - -B is number of bits for switching capacitors
 - $C_{\rm sw}$ is LSB switching capacitance; $2^{B-1}C_{\rm sw}$ is MSB switching capacitance

varactor

- $C_{\rm v}$ is minimum varactor capacitance; $K_{\rm v}C_{\rm v}$ is maximum ($K_{\rm v}$ is process constant)
- varactor range covers 2 LSB: $2C_{\rm sw} \leq 0.5(K_{\rm v}-1)C_{\rm v}$

Tank capacitance

- ullet tank capacitance is sum of $C_{
 m fix}$ and $C_{
 m tune}$
- fixed capacitance is sum of loop, load and transistor capacitances:

$$C_{\text{fix}} = C + 0.5 \left(C_{\text{L}} + C_{\text{gs}} + 4C_{\text{gd}} + C_{\text{db}} \right)$$

- tunable capacitance is sum of switching and varactor capacitances:
 - $C_{\rm tune}$ for maximum frequency: $C_{\rm tune} = 0.5 C_{\rm v}$
 - C_{tune} for minimum frequency: $C_{\text{tune}} = 2^B C_{\text{sw}} + 0.5 K_{\text{v}} C_{\text{v}}$

Resonance frequency & tuning

- capacitance constraint at maximum frequency: $C_{\rm fix} + 0.5C_{\rm v} \le C_{\rm f,max}$
- maximum frequency: $(2\pi f(1+T))^2 LC_{\rm f,max} = 1$
- capacitance at center frequency: $(2\pi f)^2 LC_{\rm f,c} = 1$
- tuning range constraint:

$$\frac{4T}{(1-T^2)^2}C_{f,c} \le C_{sw} (2^B + 2)$$

Power & area

- power: $P = V_{\rm dd}I_{\rm bias}$
- area: $A = (D + W)^2 + 2W_{nmos}L_{nmos}$ (can add area of switched capacitors, varactor)

Tank conductance & voltage swing

$$\bullet$$
 tank conductance is posynomial: $G_{\rm T} = \frac{R}{4\pi^2 f^2 L^2} + 0.5 g_{\rm o}$

• differential voltage amplitude: $V_{\rm osc} + 2V_{\rm bias} \le 2V_{\rm dd}$, $V_{\rm osc}G_{\rm T} \le I_{\rm bias}$

Phase noise

- \bullet thermal current noise power density of loop: $\overline{i_{\rm n,L}^2} = \frac{4kTR}{4\pi^2f^2L^2}$
- ullet thermal current noise power density of transistor: $\overline{i_{
 m nmos}^2} = 4kT\gamma g_{
 m m}$
- phase noise in the $1/f^2$ region:

$$N = \frac{1}{16\pi^2 f_{\text{off}}^2 C_{\text{T}}^2 V_{\text{osc}}^2} \left(\overline{i_{\text{n,L}}^2} + 0.5 \overline{i_{\text{nmos}}^2} \right)$$

. . . can add other noise terms

Loop gain and start-up

- inverse of loop gain is posynomial: $1/l = (g_{\rm o} + 2G)/g_{\rm m}$
- minimum loop gain to ensure start-up: $l \geq l^{\min}$
- bias condition for quiescent operating point: $V_{\rm bias} + V_{\rm gs} + \frac{I_{\rm bias}R}{4} \leq V_{\rm dd}$
- NMOS device models:

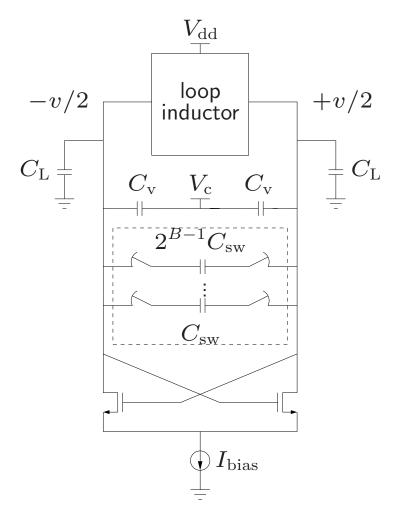
$$g_{\rm m} = 4.5 \cdot 10^{-3} W_{\rm nmos}^{0.6} L_{\rm nmos}^{-0.6} I_{\rm bias}^{0.4}$$

$$g_{\rm o} = 2.6 \cdot 10^{-10} W_{\rm nmos}^{0.4} L_{\rm nmos}^{-1.4} I_{\rm bias}^{0.6}$$

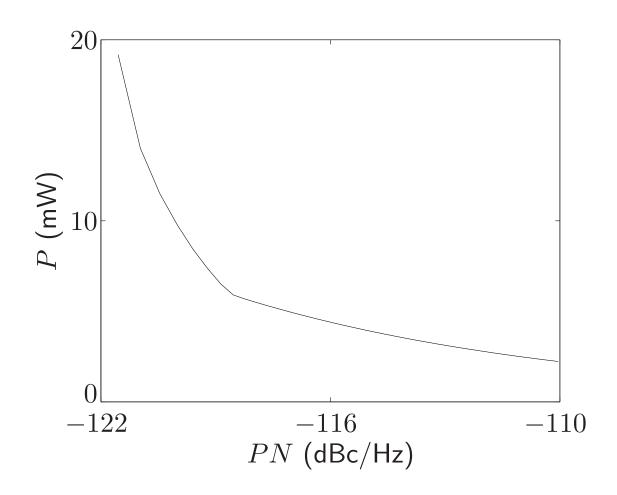
$$V_{\rm gs} = 0.34 + 1 \cdot 10^{-8} L_{\rm nmos}^{-1} + 5 \cdot 10^{2} W_{\rm nmos}^{-0.7} L_{\rm nmos}^{0.7} I_{\rm bias}^{0.7}$$

LC oscillator example

- center frequency: f = 5 GHz
- tuning range: $T = \pm 10\%$
- varactor tuning ratio: $K_{\rm v}=3$
- B = 3bits switching capacitor
- minimum loop gain: $l^{\min} = 2$
- load capacitance: $C_{\rm L}=200{\rm fF}$
- supply voltage: $V_{\rm dd} = 1.2 \rm V$
- offset frequency for phase noise: $f_{\rm off} = 600 {\rm kHz}$



Power versus phase noise trade-off



Monomial and Posynomial Fitting

A basic property of posynomials

- \bullet if f is a monomial, then $\log f(e^y)$ is **affine** (linear plus constant)
- ullet if f is a posynomial, then $\log f(e^y)$ is **convex**
- roughly speaking, a posynomial is convex when plotted on log-log plot
- midpoint rule for posynomial f:
 - let z be elementwise geometric mean of x, y, i.e., $z_i = \sqrt{x_i y_i}$
 - then $f(z) \le \sqrt{f(x)f(y)}$
- ullet a converse: if $\log \phi(e^y)$ is convex, then ϕ can be approximated as well as you like by a posynomial

Convexity in circuit design context

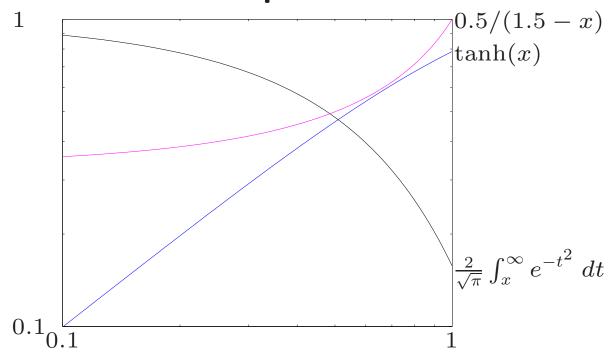
- consider circuit with design variables W_1, \ldots, W_n (say) & performance measure $\phi(W_1, \ldots, W_n)$ (e.g., power, delay, area)
- ullet two designs: $W_i^{(a)}$ & $W_i^{(b)}$, with performance $\phi^{(a)}$ & $\phi^{(b)}$
- form **geometric mean** compromise design with $W_i^{(c)} = \sqrt{W_i^{(a)}W_i^{(b)}}$, performance $\phi^{(c)}$
- ullet if ϕ is generalized posynomial, then we have $\phi^{(c)} \leq \sqrt{\phi^{(a)}\phi^{(b)}}$
- this is **not obvious**

Monomial/posynomial approximation: Theory

when can a function f be approximated by a monomial or generalized posynomial?

- form function $F(y) = \log f(e^y)$
- ullet f can be approximated by a monomial if and only if F is nearly affine (linear plus constant)
- ullet f can be approximated by a generalized posynomial if and only if F is nearly convex

Examples



- \bullet $\tanh(x)$ can be reasonably well fit by a monomial
- \bullet 0.5/(1.5-x) can be fit by a generalized posynomial
- $(2/\sqrt{\pi})\int_x^\infty e^{-t^2} dt$ cannot be fit very well by a generalized posynomial

What problems can be approximated by GGPs?

minimize
$$f_0(x)$$

subject to $f_i(x) \leq 1, \quad i = 1, \dots, m$
 $g_i(x) = 1, \quad i = 1, \dots, p$

- transformed objective and inequality constraint functions $F_i(y) = \log f_i(e^y)$ must be nearly convex
- transformed equality constraint functions $G_i(y) = \log G_i(e^y)$ must be nearly affine

Monomial fitting via log-regression

find coefficient c > 0 and exponents a_1, \ldots, a_n of monomial f so that

$$f(x^{(i)}) \approx f^{(i)}, \qquad i = 1, \dots, N$$

rewrite as

$$\log f(x^{(i)}) = \log c + a_1 \log x_1^{(i)} + \dots + a_n \log x_n^{(i)}$$

$$\approx \log f^{(i)}, \qquad i = 1, \dots, N$$

• use least-squares (regression) to find $\log c$, a_1, \ldots, a_n that minimize

$$\sum_{i=1}^{N} \left(\log c + a_1 \log x_1^{(i)} + \dots + a_n \log x_n^{(i)} - \log f^{(i)} \right)^2$$

Posynomial fitting via Gauss-Newton

find coefficients and exponents of posynomial f so that

$$f(x^{(i)}) \approx f^{(i)}, \qquad i = 1, \dots, N$$

• minimize sum of squared fractional errors

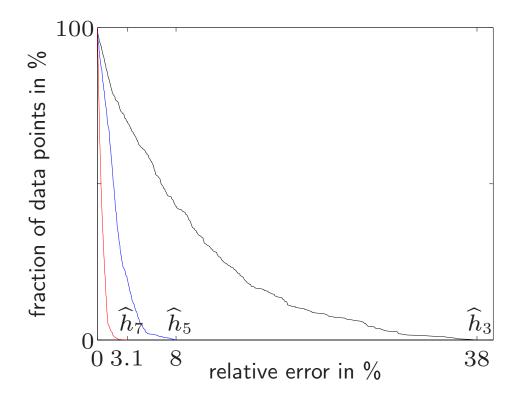
$$\sum_{i=1}^{N} \left(\frac{f^{(i)} - f(x^{(i)})}{f^{(i)}} \right)^{2}$$

can be (locally) solved by Gauss-Newton method

needs starting guess for coefficients, exponents

Posynomial fitting example

- 1000 data points from $f(x) = e^{(\log x_1)^2 + (\log x_2)^2}$ over $0.1 \le x_i \le 1$
- \bullet cumulative error distribution for 3-, 5-, and 7-term posynomial fits



A simple max-monomial fitting method

fit max-monomial

$$f(x) = \max_{k=1,\dots,K} f_k(x)$$

 $(f_1,\ldots,f_k \text{ monomials})$ to data $x^{(i)},f^{(i)}$, $i=1,\ldots,N$

simple algorithm:

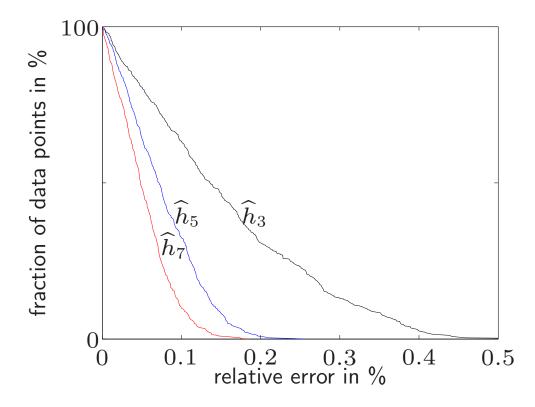
repeat

for
$$k = 1, \dots, K$$

- 1. find all data points $x^{(j)}$ for which $f_k(x^{(j)}) = f(x^{(j)})$ (*i.e.*, data points at which f_k is the largest of the monomials)
- 2. update f_k by carrying out monomial fit to these data

Max-monomial fitting example

- same 1000 data points as previous example
- cumulative error distribution for 3-, 5-, and 7-term max-monomial fits



Conclusions

Conclusions

(generalized) geometric programming

- comes up in a variety of circuit sizing contexts
- can be used to formulate a variety of problems
- admits fast, reliable solution of large-scale problems
- is good at concurrently balancing lots of coupled constraints and objectives
- is useful even when problem has discrete constraints

Approach

- most problems don't come naturally in GP form; be prepared to reformulate and/or approximate
- GP modeling is not a "try my software" method; it requires thinking
- our approach:
 - start with simple analytical models (RC, square-law, Pelgrom, . . .)
 to verify GP might apply
 - then fit GP-compatible models to simulation or measured data
 - for highest accuracy, revert to local method for final polishing

looking for keys under street light
 (not where keys were lost, but lighting is good)

• forcing problems into GP-compatible form (problems aren't GPs, but solving is good)

References

- A tutorial on geometric programming
- Digital circuit sizing via geometric programming
- Analog circuit design via geometric programming
- Convex optimization, Cambridge Univ. Press 2004

(these include hundreds of references)

available at www.stanford.edu/~boyd/research.html

Software

- MOSEK: www.mosek.com
- COPL-GP: (Yinyu Ye, in process of being re-worked): www.stanford.edu/~yyye/Col.html
- GPGLP: ftp://ftp.pitt.edu/dept/ie/GP/
- YALMIP: control.ee.ethz.ch/~joloef/yalmip.msql
- a simple matlab GP solver gp.m at Boyd's EE364 site